

FDS6994S

Dual Notebook Power Supply N-Channel PowerTrench® SyncFet™

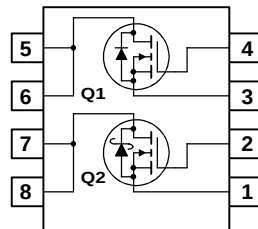
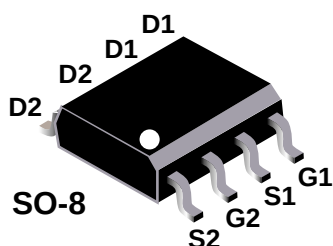
General Description

The FDS6994S is designed to replace two single SO-8 MOSFETs and Schottky diode in synchronous DC:DC power supplies that provide various peripheral voltages for notebook computers and other battery powered electronic devices. FDS6994S contains two unique 30V, N-channel, logic level, PowerTrench MOSFETs designed to maximize power conversion efficiency.

The high-side switch (Q1) is designed with specific emphasis on reducing switching losses while the low-side switch (Q2) is optimized to reduce conduction losses. Q2 also includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.

Features

- Q2:** Optimized to minimize conduction losses
Includes SyncFET Schottky body diode
 8.2A, 30V $R_{DS(on)} = 15\text{ m}\Omega @ V_{GS} = 10\text{V}$
 $R_{DS(on)} = 17.5\text{ m}\Omega @ V_{GS} = 4.5\text{V}$
- Q1:** Optimized for low switching losses
Low gate charge (85.5 nC typical)
 6.9A, 30V $R_{DS(on)} = 21\text{ m}\Omega @ V_{GS} = 10\text{V}$
 $R_{DS(on)} = 26\text{ m}\Omega @ V_{GS} = 4.5\text{V}$



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Q2	Q1	Units
V _{DSS}	Drain-Source Voltage	30	30	V
V _{GSS}	Gate-Source Voltage	±16	±16	V
I _D	Drain Current - Continuous (Note 1a)	8.2	6.9	A
	- Pulsed	30	20	
P _D	Power Dissipation for Dual Operation	2		W
	Power Dissipation for Single Operation (Note 1a)	1.6		
	(Note 1b)	1		
	(Note 1c)	0.9		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6994S	FDS6994S	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$ $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Q2 Q1	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C $I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	Q2 Q1		23 24		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	Q2 Q1			500 1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	All			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$ $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Q2 Q1	1 1	1.5 1.9	3 3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C $I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	Q2 Q1		-2 -5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 8.2\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 8.2\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 7.6\text{ A}$	Q2		10 15 11	15 24 17.5	m Ω
		$V_{GS} = 10\text{ V}, I_D = 6.9\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 6.9\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}$	Q1		16 24 19	21 33.5 26	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	Q2 Q1	30 20			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 8.2\text{ A}$ $V_{DS} = 10\text{ V}, I_D = 6.9\text{ A}$	Q2 Q1	42 41			S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	Q2 Q1		2815 800		pF
C_{oss}	Output Capacitance		Q2 Q1		540 205		pF
C_{rss}	Reverse Transfer Capacitance		Q2 Q1		210 90		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$	Q2 Q1		2.8 2.6	4.9 4.6	Ω

Electrical Characteristics (continued)

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Switching Characteristics (Note 2)

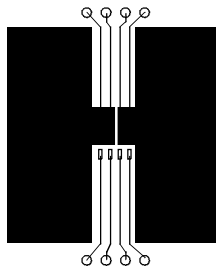
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\ \Omega$	Q2		11	20	ns
			Q1		11	20	
t_r	Turn-On Rise Time		Q2		8	16	ns
			Q1		7	14	
$t_{d(off)}$	Turn-Off Delay Time		Q2		50	80	ns
			Q1		27	43	
t_f	Turn-Off Fall Time		Q2		17	31	ns
			Q1		4	8	
Q_g	Total Gate Charge	Q2: $V_{DS} = 15\text{ V}$, $I_D = 7.9\text{ A}$, $V_{GS} = 5\text{ V}$	Q2		25	35	nC
			Q1		8	12	
Q_{gs}	Gate-Source Charge	Q1: $V_{DS} = 15\text{ V}$, $I_D = 6.5\text{ A}$, $V_{GS} = 5\text{ V}$	Q2		6		nC
			Q1		3		
Q_{gd}	Gate-Drain Charge		Q2		7		nC
			Q1		3		

Drain-Source Diode Characteristics and Maximum Ratings

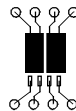
I_S	Maximum Continuous Drain-Source Diode Forward Current		Q2			2.3	A
			Q1			1.3	
t_{RR}	Reverse Recovery Time	$I_F = 8.2\text{ A}$, $dI_F/dt = 300\text{ A}/\mu\text{s}$ (Note 3)	Q2		25		ns
Q_{RR}	Reverse Recovery Charge				19		nC
t_{RR}	Reverse Recovery Time	$I_F = 6.9\text{ A}$, $dI_F/dt = 100\text{ A}/\mu\text{s}$ (Note 3)	Q2		23		ns
Q_{RR}	Reverse Recovery Charge				10		nC
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2.3\text{ A}$ (Note 2)	Q2		0.4	7	V
		$V_{GS} = 0\text{ V}$, $I_S = 1.3\text{ A}$ (Note 2)	Q1		0.53	1.2	

Notes:

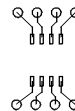
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in^2 pad of 2 oz copper



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty Cycle < 2.0%

3. See "SyncFET Schottky body diode characteristics" below.

Typical Characteristics for Q2

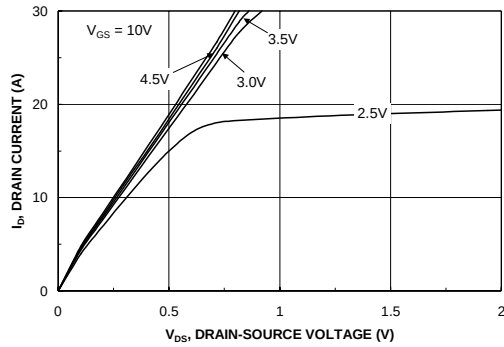


Figure 1. On-Region Characteristics.

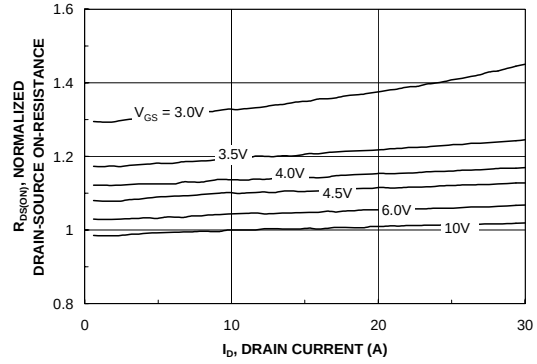


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

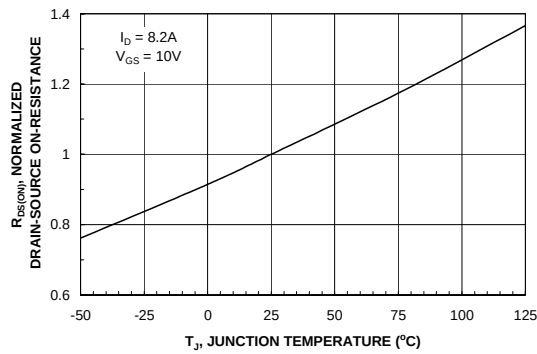


Figure 3. On-Resistance Variation with Temperature.

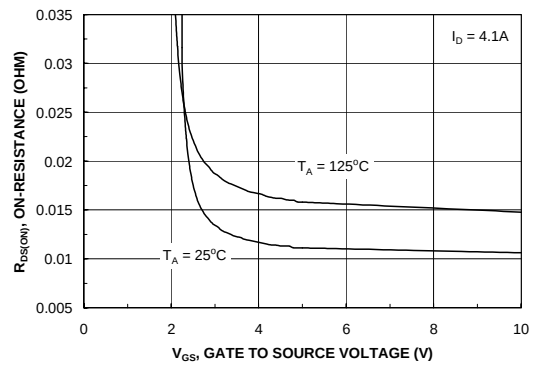


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

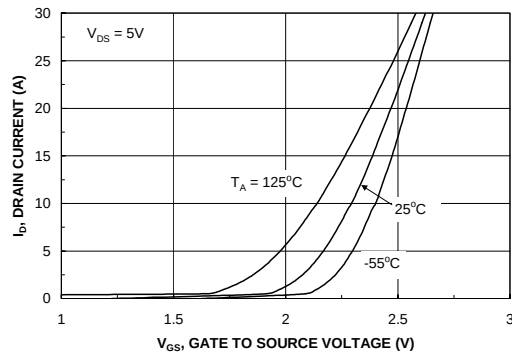


Figure 5. Transfer Characteristics.

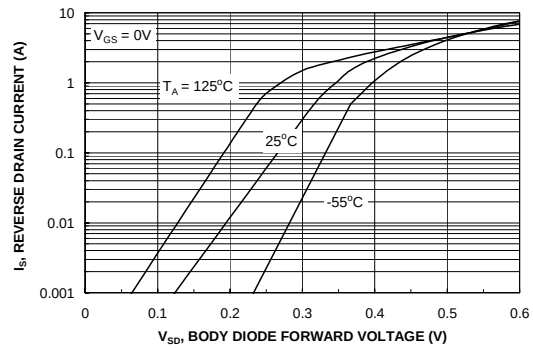


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics for Q2

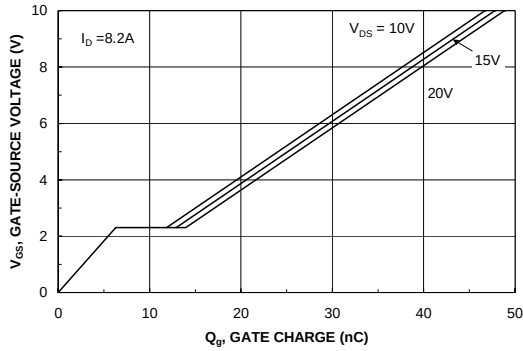


Figure 7. Gate Charge Characteristics.

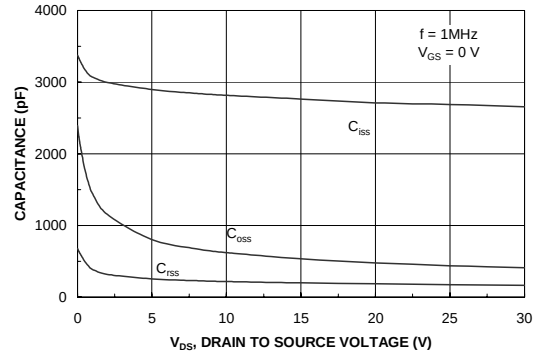


Figure 8. Capacitance Characteristics.

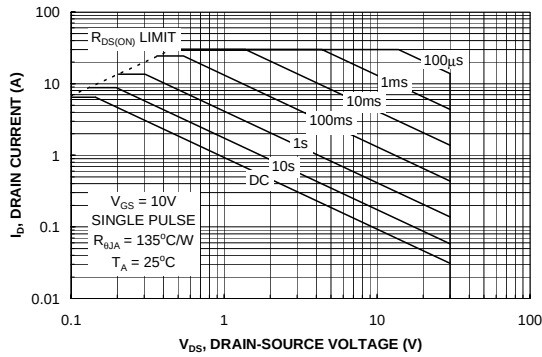


Figure 9. Maximum Safe Operating Area.

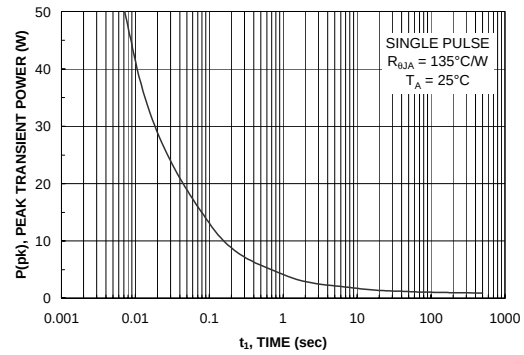


Figure 10. Single Pulse Maximum Power Dissipation.

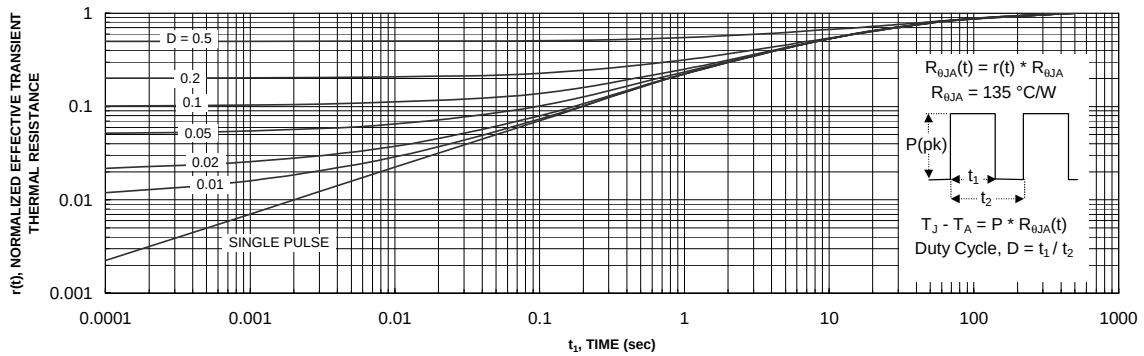


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics for Q1

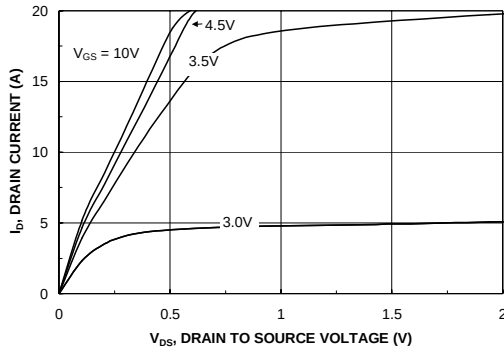


Figure 11. On-Region Characteristics.

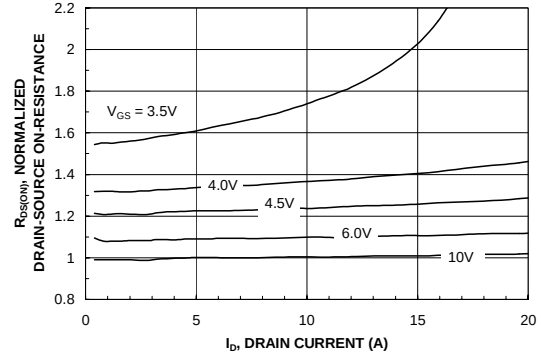


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

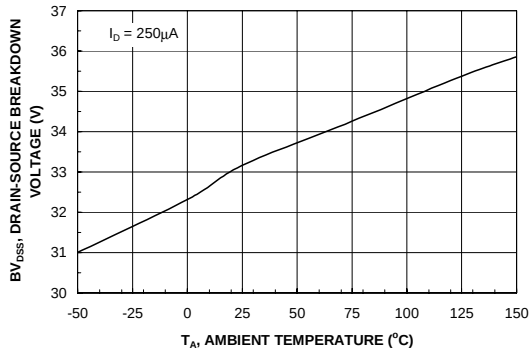


Figure 13. On-Resistance Variation with Temperature.

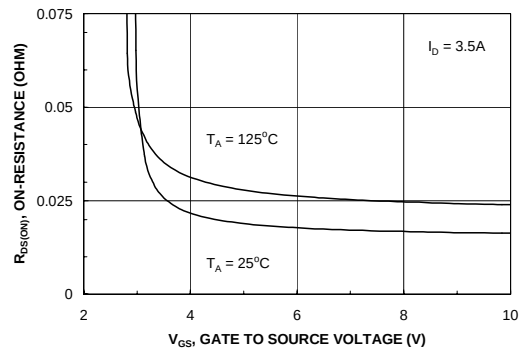


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

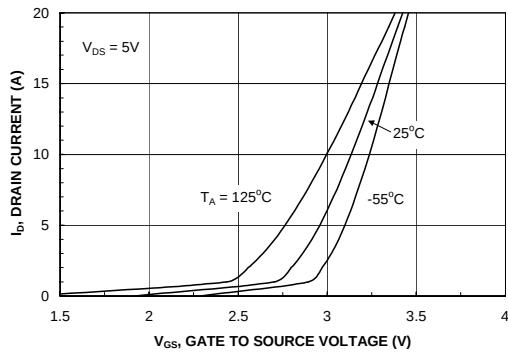


Figure 15. Transfer Characteristics.

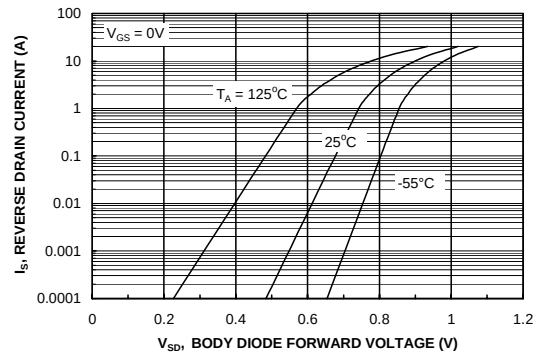


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics Q1

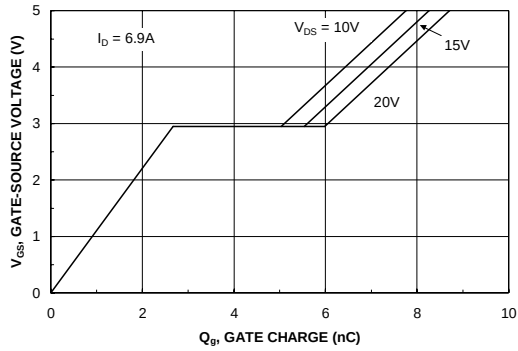


Figure 17. Gate Charge Characteristics.

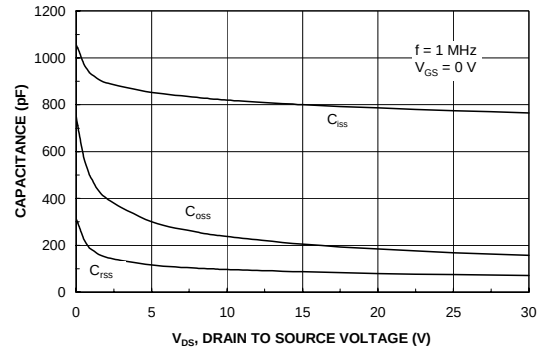


Figure 18. Capacitance Characteristics.

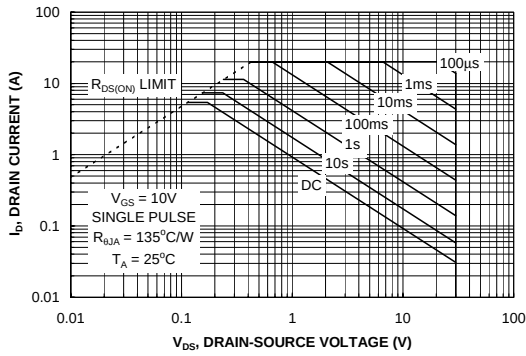


Figure 19. Maximum Safe Operating Area.

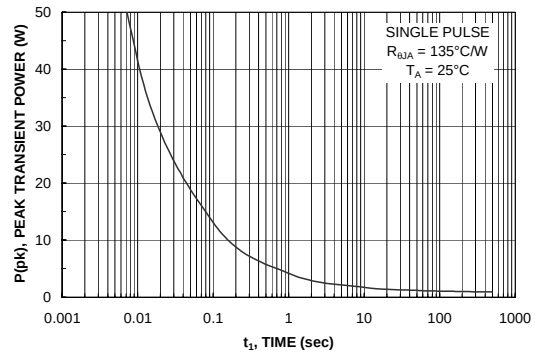


Figure 20. Single Pulse Maximum Power Dissipation.

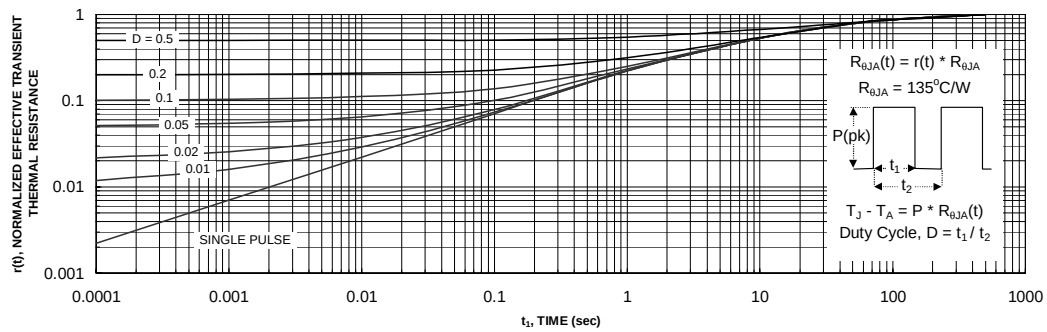


Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics (continued) This section copied from FDS6984S datasheet

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 22 shows the reverse recovery characteristic of the FDS6994S.

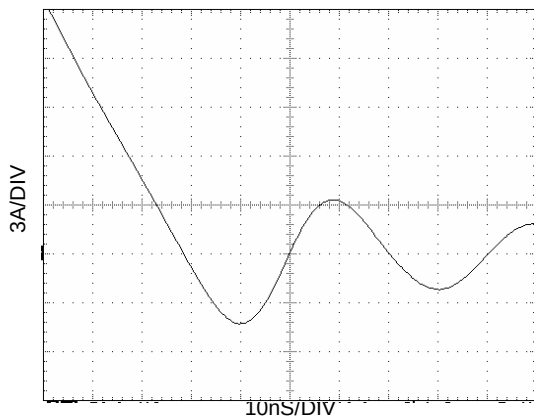


Figure 22. FDS6994S SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 23 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS6690A).

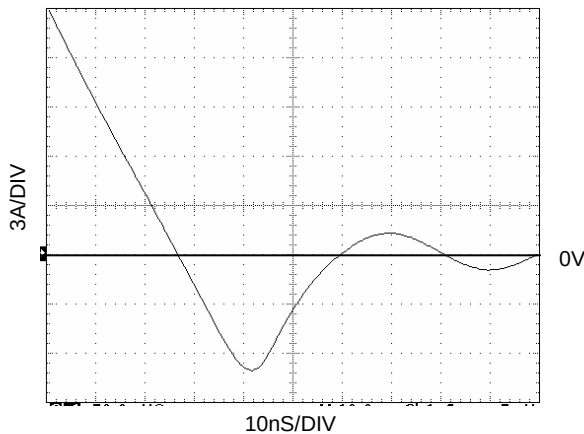


Figure 23. Non-SyncFET (FDS6690A) body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

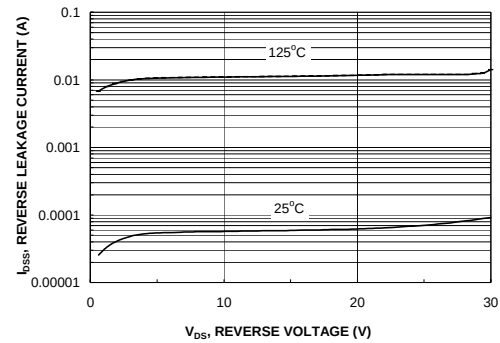


Figure 24. SyncFET body diode reverse leakage versus drain-source voltage and temperature.